

GaN MMIC Power Amplifier 6-18GHz

Features

• Frequency: 6-18GHz

• Small Signal Gain: 28dB Typical Power Gain: 15dB Typical • Gain Flatness: ±4.0dB Typical

• Psat: 40dBm Typical

• PAE:25%

• Supply Voltage:

VD=+28V@0.85A,VG=-1.6V

• Input/Output: 50Ω

• Die Size: 4.2 x 3.15 x 0.1mm

Typical Applications

- · Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications

 $TA = +25^{\circ}C$, VD=+28V, IDD = 0.85A Typical

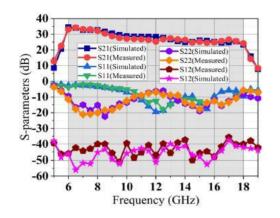
| Parameters | Min. | Тур. | Max. | Units |
|-------------------------------|------|------|------|-------|
| Frequency | 6 | | 18 | GHz |
| Small Signal Gain | | 28 | | dB |
| Power Gain | | 15 | | dB |
| Gain Flatness | | ±4.0 | | dB |
| P1dB - Output 1dB Compression | | / | | dBm |
| Psat - Saturated Output Power | | 40 | | dBm |
| PAE-Power Added Efficiency | | 25 | | % |
| Input Return Loss | | -8 | | dB |
| Output Return Loss | | -8 | | dB |



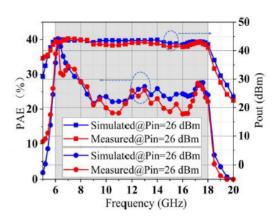
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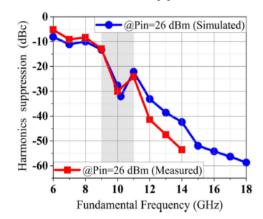
S-parameters vs. Frequency



PAE vs. Frequency



Harmonics Supperssion





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Absolute Maximum Ratings

| Drain Bias Voltage (VD) | +30V |
|------------------------------|------------------|
| Gate Bias Voltages(VG) | -5V |
| RF Input Power (RFIN)@(+28V) | +30dBm |
| Channel Temperature | 225 °C |
| Junction Temperature | 310 °C |
| Operating Temperature | -55°C to +85 °C |
| Storage Temperature | -55°C to +175 °C |

Typical Supply Current vs. VD,VG

| VD (V) | VG (V) | IDD (mA) |
|--------|--------|----------|
| +28 | -1.6 | 850 |



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

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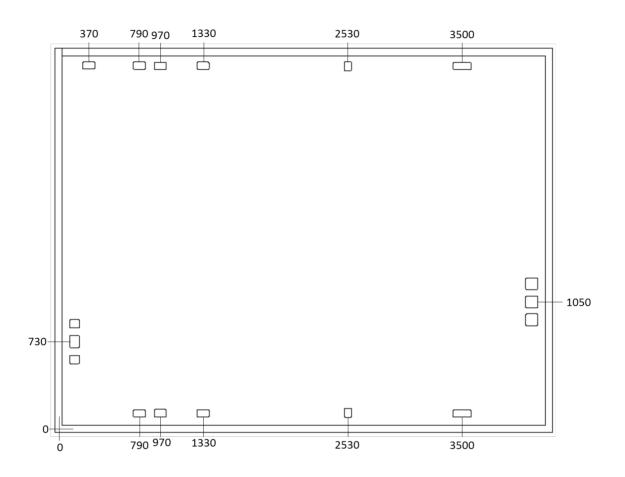


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Outline Drawing:

All Dimensions in µm



Notes:

1. Die size: 4200*3150 μm

Input RF Pad size: 100*85 μm
Output RF Pad size: 100*100 μm
VG1,2 pad size: 100*62 μm
VD1,2 pad size: 100*62 μm
VG3 pad size: 63*75 μm
VD3 pad size: 150*62 μm

8. GSG: 150 µm

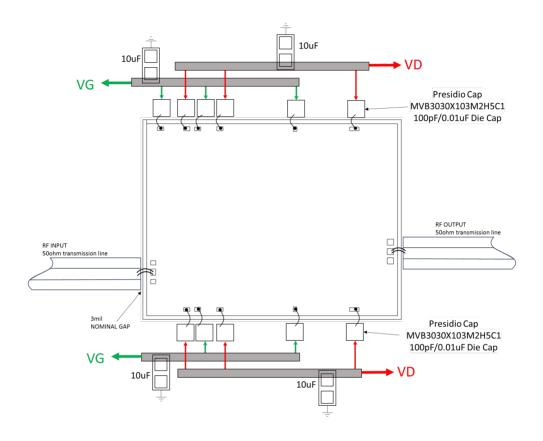
9. Bond pad metalization: Gold 10.Backside metalization: Gold



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Assembly Drawing



| No. | Mnemonic | Description |
|-----|------------|--|
| 1 | RF IN | Signal input terminal, connected to 50Ω circuit. |
| 2 | RF OUT | Signal output terminal, connected to 50Ω circuit. |
| 3 | VD | Drain voltage, bias network is required; see Application Circuit on. |
| 4 | VG | Gate voltage, bias network is required; see Application Circuit on. |
| 5 | Die Bottom | Die bottom must be connected to RF and dc ground. |

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